

SILICON NPN PHOTO DETECTOR

DESCRIPTION:

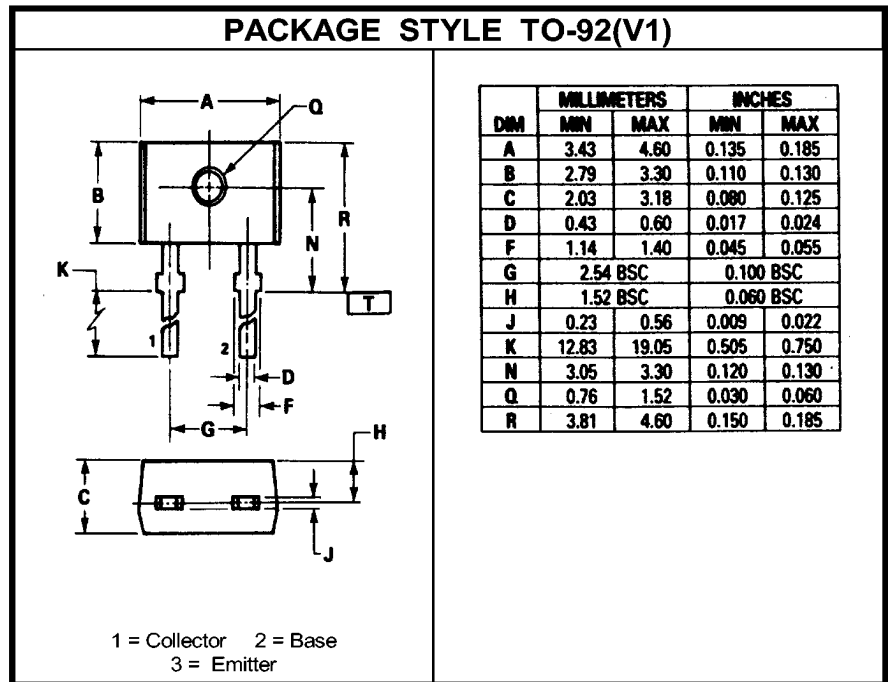
The **2N5777(MOD.)** is Designed for General Purpose Industrial Photo Detector Applications.

FEATURES:

- High Sensitivity
- Economical TO-92 compatible package

MAXIMUM RATINGS

I_L	250 mA
V_{CEO}	40 V
P_{DISS}	250 mW @ $T_C = 25^\circ C$
T_J	-40 to +100 $^\circ C$
T_{ST}	-40 to +100 $^\circ C$



CHARACTERISTICS $T_A = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_D	$I_C = 1 \text{ mA}$	40	60		V
I_L	$V_{CE} = 12 \text{ V}$			100	nA
	$V_{CE} = 5 \text{ V}$ $H = 500 \mu\text{W}/\text{cm}^2$	5			mA
C_{CE}	$V_{CE} = 10 \text{ V}$ $f = 1 \text{ MHz}$		3.2		pF
$V_{CE(sat)}$	$V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ mA}$ $H = 500 \mu\text{W}/\text{cm}^2$		0.75	1.0	V
t_{on}	$V_{CE} = 10 \text{ V}$ $R_L = 100 \Omega$ $H = 500 \mu\text{W}/\text{cm}^2$		125		μS
t_{off}	$V_{CE} = 10 \text{ V}$ $R_L = 100 \Omega$ $H = 500 \mu\text{W}/\text{cm}^2$		150		μS

ADVANCED SEMICONDUCTOR, INC.

REV. A

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